

FS10ASJ-06F

High-Speed Switching Use Nch Power MOS FET

> REJ03G0241-0200 Rev.2.00 Dec 19, 2008

Features

Drive voltage: 4 V

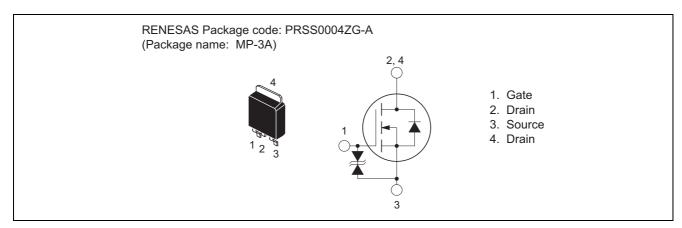
 V_{DSS} : 60 V

 $r_{\rm DS(ON)\,(max)}$: 70 m Ω

 $I_D: 10 A$

• Recovery Time of the Integrated Fast Recovery Diode (TYP.): 30 ns

Outline



Applications

Motor control, lamp control, solenoid control, DC-DC converters, etc.

Maximum Ratings

 $(Tc = 25^{\circ}C)$

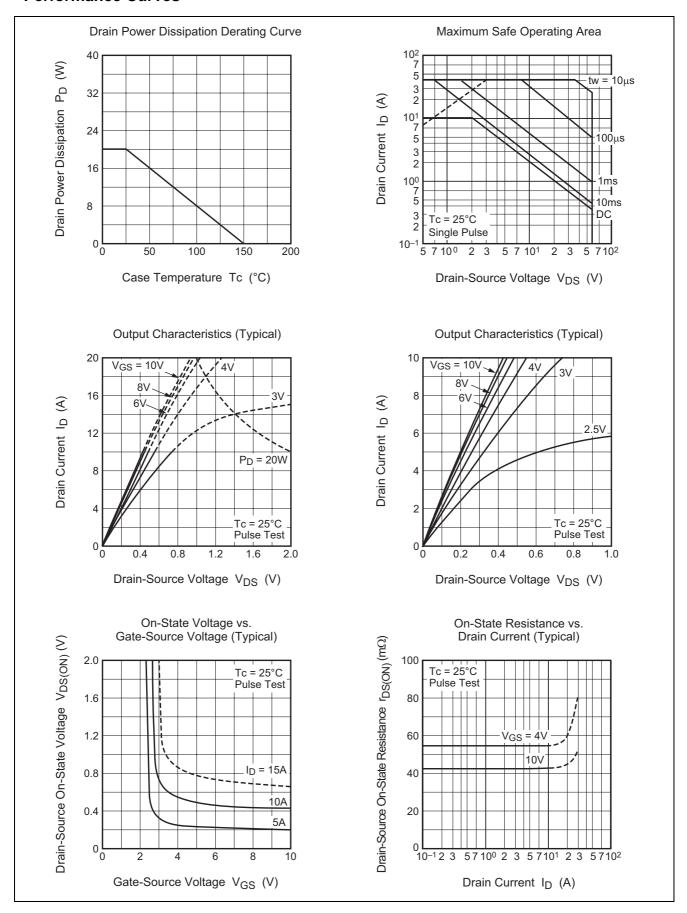
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V _{DSS}	60	V	V _{GS} = 0 V
Gate-source voltage	V _{GSS}	±20	V	V _{DS} = 0 V
Drain current	I _D	10	Α	
Drain current (Pulsed)	I _{DM}	40	Α	
Avalanche current (Pulsed)	I _{DA}	10	А	L = 50 μH
Source current	Is	10	А	
Source current (Pulsed)	I _{SM}	40	А	
Maximum power dissipation	P _D	20	W	
Channel temperature	Tch	- 55 to +150	°C	
Storage temperature	Tstg	- 55 to +150	°C	
Mass	_	0.32	g	Typical value

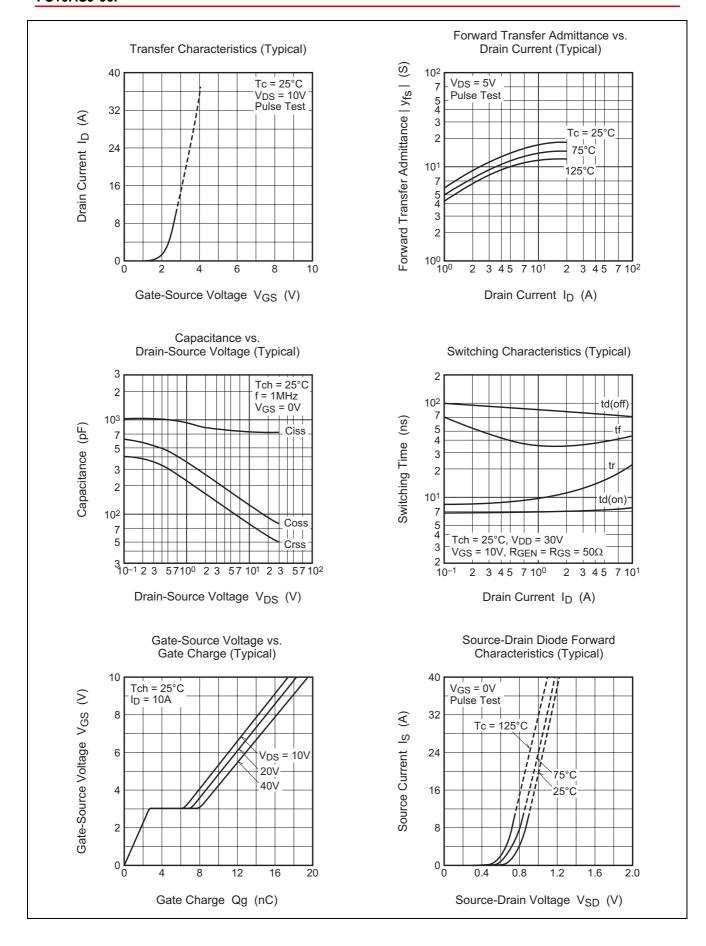
Electrical Characteristics

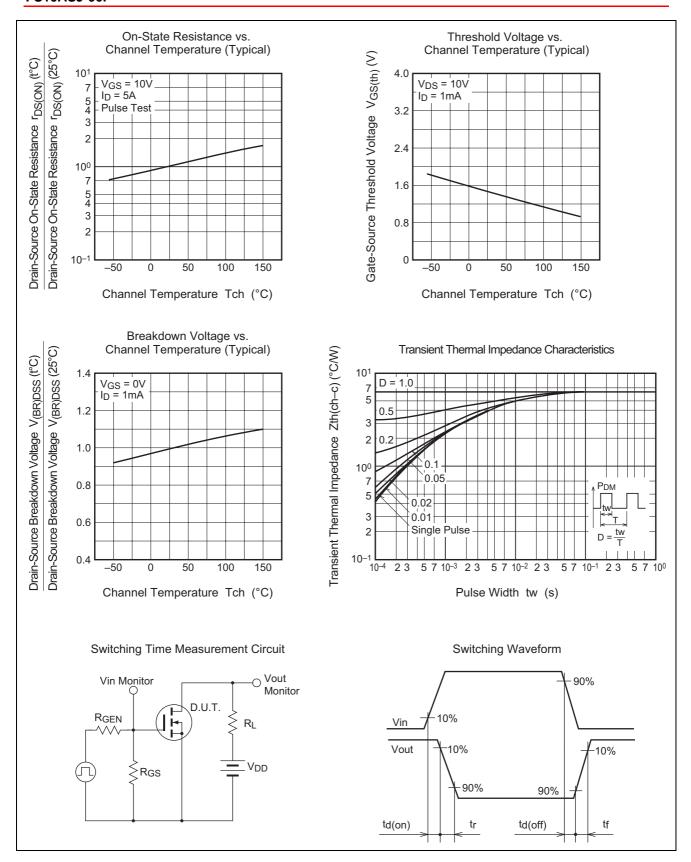
 $(Tch = 25^{\circ}C)$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions	
Drain-source breakdown voltage	V _{(BR)DSS}	60	_	_	V	I _D = 1 mA, V _{GS} = 0 V	
Gate-source breakdown voltage	V _{(BR)GSS}	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0 \ V$	
Drain-source leakage current	I _{DSS}	_	_	100	μΑ	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$	
Gate-source leakage current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	
Gate-source threshold voltage	$V_{GS(th)}$	1.0	1.5	2.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$	
Drain-source on-state resistance	r _{DS(ON)}	_	53	70	mΩ	$I_D = 5 \text{ A}, V_{GS} = 10 \text{ V}$	
Drain-source on-state resistance	r _{DS(ON)}	_	66	86	mΩ	$I_D = 5 A, V_{GS} = 4 V$	
Drain-source on-state voltage	V _{DS(ON)}	_	0.27	0.35	V	$I_D = 5 \text{ A}, V_{GS} = 10 \text{ V}$	
Forward transfer admittance	y _{fs}	_	13	_	S	$I_D = 5 \text{ A}, V_{DS} = 10 \text{ V}$	
Input capacitance	Ciss	_	750	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$	
Output capacitance	Coss	_	130	_	pF	f = 1MHz	
Reverse transfer capacitance	Crss	_	80	_	pF		
Turn-on delay time	t _{d(on)}	_	7	_	ns	$V_{DD} = 30 \text{ V}, I_D = 5 \text{ A},$	
Rise time	t _r	_	18	_	ns	$V_{GS} = 10 V$,	
Turn-off delay time	t _{d(off)}	_	70	_	ns	$R_{GEN} = R_{GS} = 50 \Omega$	
Fall time	t _f	_	35	_	ns	1	
Source-drain voltage	V _{SD}	_	1.0	1.5	V	I _S = 5 A, V _{GS} = 0 V	
Thermal resistance	Rth(ch-c)	_	_	6.25	°C/W	Channel to case	
Reverse recovery time	t _{rr}	_	30	_	ns	$I_S = 10 \text{ A}, \text{ dis/dt} = -100 \text{ A/}\mu\text{s}$	

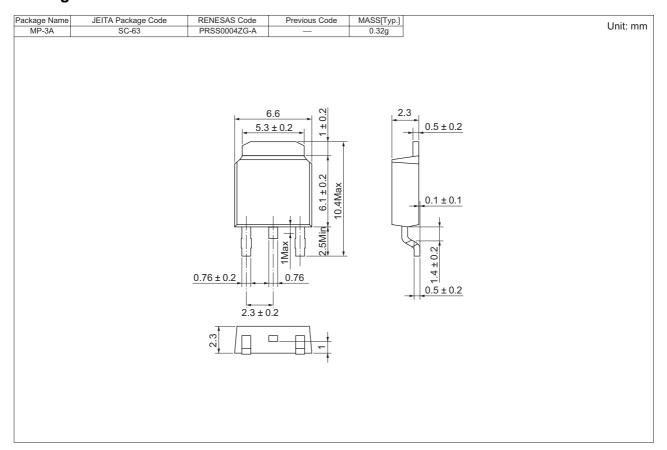
Performance Curves







Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FS10ASJ-06F-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	FS10ASJ-06F

Note: Please confirm the specification about the shipping in detail.

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